





Fundamentals of Layout Design for Electronic Circuits



Jens Lienig · Juergen Scheible

# Fundamentals of Layout Design for Electronic Circuits



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# Foreword

The advances in technology and the continuation of Moore's law mean that we can now make transistors that are smaller than human cells. We can also integrate trillions of these transistors in a single chip and expect that all these transistors turn on and off a few billion times a second synchronously. This engineering feat has been made possible by the ingenuity of computer scientists and mathematicians, who design the algorithms to enhance the performance of the computers, and the inventiveness of engineers who are able to build these complex and intricate systems. Generating the schematic network of a trillion-transistor circuit inside a CAD program is enormously difficult—getting it laid out during physical design so that the circuit works in real silicon flawlessly is, however, the real challenge we face today.

I have been teaching courses on physical design for almost two decades to computer science and electrical engineering students. I have always had to carefully walk the tight rope that separates the teaching of theory from practice. One of the most difficult parts has been finding a textbook that gives a balanced view between theory and actual design. On one hand, the current and future engineers need to know the design algorithms and how to deal with the ever-increasing number of transistors. On the other hand, they need to know how to fabricate ICs and what are the constraints that exist because of the ever-reducing transistor sizes. And here this book comes in: It covers the theoretical concepts and the technical know-how in a practical, application-oriented manner for every layout engineer. It starts with silicon material and IC fabrication and how the silicon material can be manipulated to make microelectronic devices and operate the circuit. Then, the book comes back to changes that happen in the silicon as a result of circuit operation. All of these topics are covered in a practical manner with lots of demonstrations to cement the concepts.

This book is able to connect the theoretical world of design automation to the practical world of the electronic-circuit layout generation. The text focuses on the physical/layout design of integrated circuits (ICs), but also covers printed circuit boards (PCBs) where needed. It takes the reader through a journey starting with how we transform silicon into reliable devices, discusses how we are able to

perform such engineering feats, and the important practical considerations during this process. Then, the book bridges to how these vast and complicated physical structures can be best represented as data and how to turn this data back into a physical structure. It continues with the discussion of the models, styles and steps for physical design to give a big picture of how these designs are made, before going into special hands-on requirements for layout design of analog ICs. Finally, it ends by discussing practical considerations that could extend the reliability of the circuits, giving the designers and engineers a 360-degree point of view of the physical design process.

I have known Jens Lienig through his work and books for many years. In his books, he first captures the reader's attention by giving a big picture, with examples and analogies, that provides the reader with an intuitive understanding of the topics to come. Only then does he go into the details, providing the depth of knowledge needed to design high performing systems. Through this combination, his readers are able to understand the material, remember the details, and use them to create new ideas and concepts. This, along with his genuine care for his readers, vast knowledge of the field and practical experience, makes Prof. Lienig the ideal person to write such a book-and he has found the perfect match: Juergen Scheible, who has a wealth of theoretical and practical experience in designing commercial circuits. His extensive experiences as the Head of the IC Layout Department for Bosch means that he has been responsible for layout design of not only a whole slew of designs including smart power chips, sensing circuits and RF designs, but also creating new design flows to adapt to ever-changing technologies. When it comes to design, Prof. Scheible knows all the tricks that come from years of industrial experience-the multitude of rules and constraints one must consider when drawing a layout in a given technological framework. The combined experience and knowledge of these two authors have made a great tapestry of theory and practice, and hence, the resulting book is a must-read for every layout engineer.

I am delighted to write this foreword not only because I have the highest regard for both authors, but also because I cannot wait to use the book for teaching physical design. The combined expertise of the authors and the attention they have paid to theory and practice, big picture and detail, illustrative examples and written text, make this book the perfect go-to resource for students and engineers alike.

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# Preface

When an engineer in a London Post Office got tired of sorting hundreds of tangled cables between their connectors, he filed a patent named "Improvements in or Connected with Electric Cables and the Jointing of the Same" in 1903—probably without foreseeing the broad implications of his "flat foil conductors laminated to an insulating board". Thus was born the *printed circuit board* (*PCB*), which became an engineering success. The first boards required extreme manufacturing skills—electronic devices were fixed between springs and electrically connected by rivets on Pertinax. Copper-laminated insulating layers were introduced in 1936, leading the way to reliable, mass-produced printed circuit boards. These boards enabled the manufacture of affordable electronic devices, such as radios, which have become indispensable items in everyone's home ever since.

The invention of miniature vacuum tubes in 1942 started the first generation of modern electronics. The earliest large-scale computing device, the Electronic Numerical Integrator and Computer (ENIAC), contained an impressive 20,000 vacuum tubes.

In 1948, the invention of the transistor kickstarted the second generation of computing devices. These transistors proved to be smaller, cooler and much more reliable than their predecessor vacuum tubes, enabling truly portable electronic gadgets, such as small transistor radios.

The 1960s saw the dawn of the third generation of electronics, ushered in by the development of *integrated circuits (ICs)*. Together with semiconductor memories, they enabled increasingly complex and miniaturized system designs. Subsequently, we witnessed the first microprocessor in 1971, followed soon thereafter by a host of technical breakthroughs whose impact remains evident today. In 1973, Motorola developed the first prototype mobile phone, in 1976 Apple Computer introduced the *Apple I*, and in 1981 IBM introduced the *IBM PC*. These developments fore-shadowed the *iPhones* and *iPads* that became ubiquitous at the turn of the twenty-first century, followed by intelligent, cloud-based electronics that complement, facilitate, and enhance our lives today. These days, even the cheapest smartphone contains more transistors than there are stars in the Milky Way!

This spectacular success in the art of engineering relies on a crucial step: transforming an abstract, yet increasingly complex circuit description into a detailed geometric layout that can subsequently be manufactured "for real" and without flaws. This step, referred to as layout design-or physical design, as it is also known in the industry and which is the term we use in this book-is the final stage in every electronic circuit design flow. All of the instructions necessary for fabricating PCBs and ICs must be generated in this step. Essentially, all components in the abstract circuit description, consisting of the device symbols and the wire connections between them, are translated into formats that describe geometric objects, such as footprints and drilling holes (for PCBs) or mask layout patterns comprising billions of rectangular shapes (for ICs). These blueprints are then used during fabrication to "magically create" the physical electrical network on the surface of a silicon chip in the case of an IC-which performs exactly the same functions as envisioned in the initial circuit description when electrons are sent through the system. Without this physical design stage, we would not have even the simplest radios, let alone laptops, smartphones or the myriad of electronic devices we take for granted nowadays.

Physical design was once a fairly straightforward process. Starting with a netlist that describes the logical circuit components and interconnections, a technology file, and a device library, a circuit designer would use floorplanning to determine where different circuit parts should be placed, and then the cells and devices would be arranged and connected in the so-called place and route step. Any circuit and timing problems would be solved by iteratively improving the layout locally.

Times have changed; if previous generations of circuit designs represented complexity analogous to towns and villages, current-generation designs cover entire countries. For example, if the wires in one of today's ICs, such as found in a smartphone, were to be laid out with regular street sizes, the area of the resulting chips would stretch over the continental U.S. and Canada combined, covered entirely with streets shoulder-to-shoulder! Hence, today's multi-billion transistor circuits and heterogeneous stacks of printed circuit boards require a far more complex physical design flow. Circuit descriptions are *partitioned* first in order to break down complexity and to allow parallel design. Once we have arranged the contents and interfaces of the partitions during *floorplanning*, these blocks can be handled independently. *Placement* of devices is the first step, followed by *routing* their connections. *Physical verification* checks and enforces timing and other constraints, and multiple measures are applied in a *post layout process* to ensure manufacturability of the IC and PCB layout.

The field of physical/layout design has grown well beyond the point where a single individual can handle everything. Constraints to be considered during layout generation have become extremely complex. The stakes are high: one missed reliability check can render a multi-million-dollar design useless. The fabrication facility to produce a single technology node can easily cost over a billion dollars. Research papers describe solutions to a myriad of these problems; their sheer volume, however, renders it impossible for engineers to keep pace with the latest developments.

Preface

Given the high stakes and the incredible complexity, there is a pressing need to temporarily step back from these rapid developments and to consider the *funda-mentals* of this extremely broad and complex design stage. Students need to learn and understand the basics behind today's complicated layout steps—the "why" and "how", not just the "what". Engineers and professionals alike need to refresh their knowledge and broaden their scope as new technologies compete for application. With Moore's law and thus, continuous down-scaling being replaced by novel and heterogeneous technologies, new physical design methodologies enter the field. To successfully master these challenges requires sound knowledge of physical design's basic methods, constraints, interfaces and design steps. This is where this book comes in.

After a thorough grounding in general electronic design in Chap. 1, we introduce the basic technology know-how in Chap. 2. This knowledge lays the foundation for understanding the multiple constraints and requirements that make physical design such a complicated process today. Chapter 3 looks at layout generation "from the outside"—what are its interfaces, how and why do we need design rules and external libraries? Chapter 4 introduces physical design as a complete end-to-end process with its various methodologies and models. Chapter 5 then dives into the individual steps involved in generating a layout, including its multifarious verification methodologies. Chapter 6 introduces the reader to the unique layout techniques needed for analog design, before Chap. 7 elaborates on the increasingly critical topic of improving the reliability of generated layouts.

This book is the result of many years of teaching layout design, combined with industrial experience gained by both authors before entering academia. Chapters 1–7 are well structured for teaching a two-semester class of layout/physical design. For use in a one-semester class, Chap. 1 (introduction) and Chap. 2 (technology) can be assigned for self-study, with instruction starting with Chap. 3 (interfaces), followed by design methodologies (Chap. 4) and design steps (Chap. 5). Alternatively, Chap. 4 can also be used as an effective starting point, followed by the detailed design steps of Chap. 5, intermittently extended with material from the respective interfaces, design rules and libraries presented in Chap. 3. All figures of the book are available for download at www.springer.com/9783030392833.

A book of such extensive scope and depth requires the support of many. The authors wish to express their warm appreciation and thanks to all who have helped produce this publication. We would like to mention in particular Martin Forrestal for his key role in writing a proper English version of our manuscript. Special thanks go to Dr. Mike Alexander who greatly assisted in the preparation of the English text. His knowledge on the subject matter of this book has been appreciated. We thank Dr. Andreas Krinke, Kerstin Langner, Dr. Daniel Marolt, Dr. Frank Reifegerste, Matthias Schweikardt, Dr. Matthias Thiele, Yannick Uhlmann, and Tobias Wolfer for their many contributions. Our warm appreciation is also due to Petra Jantzen at Springer for being very supportive and going beyond her call of duty to help out with our requests.

Rapid progress will continue apace in layout design in the years to come, perhaps by some of the readers of this humble book. The authors are always grateful for any comments or ideas for the future development of the topic, and wish you good luck in your careers.

Dresden, Germany Reutlingen, Germany Jens Lienig Juergen Scheible

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# Chapter 1 Introduction



*Layout design*—or *physical design*, as it is also known in the industry and referred to throughout the book—is the final step in the design process for an electronic circuit. It aims to produce all information necessary for the fabrication process to follow. In order to achieve this, all components of the logical design, such as cells and their connections, must be generated in a geometric format (typically, as collections of rectangles), which is used to create the microscopic devices and connections during fabrication.

This chapter gives a sound introduction to the technologies, tasks and methodologies used to design the layout of an electronic circuit. With this basic design knowledge as a foundation, the subsequent chapters then delve deeper into specific constraints and aspects of physical design, such as semiconductor technologies (Chap. 2), interfaces, design rules and libraries (Chap. 3), design flows and models (Chap. 4), design steps (Chap. 5), analog design specifics (Chap. 6), and finally reliability measures (Chap. 7).

In Sect. 1.1, we introduce several of the most common fabrication technologies for electronic systems. The central topic of this book is the physical design of integrated circuits (aka *chips*, ICs) but hybrid technologies and printed circuit boards (PCBs) are also considered. In Sect. 1.2 of our introduction, we examine in more detail the significance and peculiarities of this related branch of modern electronics—also known as *microelectronics*. In Sect. 1.3, we then consider the physical design of both integrated circuits and printed circuits boards with a specific emphasis on their primary design steps. After these opening sections, we close the introductory chapter in Sect. 1.4 by presenting our motivation for this book and describing the organization of the chapters that follow.

# **1.1 Electronics Technologies**

All electronic circuits comprise *electronic devices* (transistors, resistors, capacitors, etc.) and the metallic interconnects that electrically connect them. There is, however, a wide range of different fabrication technologies available to physically realize such electronic devices; these technologies can be classified into three main groups:

- Printed circuit board technology, which can be subdivided in
  - Through-hole technology (THT),
  - Surface-mount technology (SMT),
- Hybrid technology, often subdivided in
  - Thick-film technology,
  - Thin-film technology,
- Semiconductor technology, subdivided in
  - Discrete semiconductor components,
  - Integrated circuits.

To each of these technologies are added myriad extra features and custom designs for different use cases. Take, for example, automobile electronics, where a very high degree of robustness is required, or cellphones, where extreme compactness is a key requirement. We next examine the most important of these technologies in further detail.

### 1.1.1 Printed Circuit Board Technology

The *printed circuit board* (*PCB*) is the most widely used technology for electronic packaging. It mechanically supports and electrically connects electronic devices that are typically soldered onto the PCB.

#### **Circuit Board**

The basic element is an electrically isolated circuit board, known as the substrate core, and typically made of glass-fiber-reinforced epoxy resin. Everybody has seen this green board at some point. Papers stabilized with phenolic resins are also an option. (This approach was particularly widespread in the early years of electronics.) Paper-based circuit boards are only suitable for very low-spec applications, are rarely used anymore, and are not covered further in this book.

The circuit board has two primary functions: (i) to provide the foundation upon which the electronic devices are physically mounted, and (ii) to provide a surface upon which the interconnects for electrically connecting the devices can be constructed.

The interconnects are etched out of a metallic layer that has been applied to the substrate surface. The metal layer is made of copper and can be applied to one side

of the circuit board, or to both sides. Copper is the material of choice here, as it has several very beneficial properties: (i) it is an excellent electrical conductor; (ii) it lends itself well to etching; and (iii) it can be soldered easily. (Devices are soldered in place on the board, and simultaneously the chip pins are electrically connected to the interconnects on the board with solder.)

#### **Fabricating Interconnects**

How interconnects are fabricated is visualized in Fig. 1.1 and explained below with reference to steps (a) to (i) in the figure. The substrate core that is the foundation of the board is sometimes also referred to as the *carrier substrate*, as it "carries" (i.e., "holds" in place) the electronic devices and interconnects.

A substrate core is first coated with copper, and then a layer of photoresist is applied (a to c). The photoresist has a special property, namely that after exposure to light, it can be dissolved with a fluid called the *developer*. In the next step we use a *mask*, which is a (transparent) glass plate onto which the image of the desired interconnect has been applied as an opaque layer to the bottom surface of the glass plate (shown in black in Fig. 1.1d).

This mask is then positioned over the PCB (d) and exposed with light (illuminated sectors in yellow and shaded sectors in gray, Fig. 1.1e). The shaded area produces an image of the desired interconnect on the PCB. The resist at the exposed areas thus becomes dissolvable (the areas in pale blue in Fig. 1.1f); this exposed resist can then be dissolved and washed away with the developer. The remaining unexposed



Fig. 1.1 Sectional view of the creation of interconnects on a printed circuit board (PCB) by photolithography and subsequent etching

areas retain their photoresist, which protects the copper layer underneath against etching in the next step (g), such that the etching agent only removes the copper on the unprotected areas. We say the resist "masks" the etching. After etching, only the copper remains at the prior unexposed areas; the remaining photoresist is washed away with a suitable fluid (h). Through this process, we have created in the copper layer the interconnect structure that was patterned on the mask (i).

When only a few PCBs are required, such as for prototypes, the interconnects are sometimes not formed by etching, but by mechanically milling the metal layer.

#### **Multi-Layer Printed Circuit Boards**

Boards can be constructed of several stacked substrate cores, and in this case are called *multilayer PCBs*. Figure 1.2 shows an example of a multilayer board, consisting of three cores and six routing layers (the top and bottom of each of the three cores). The cores are glued together with a bonding agent, which also acts as an electrical isolator between the opposing copper layers of neighboring substrate cores, to prevent short circuits.

Plated-through contacts, known as *vias*, are then used to electrically connect different routing layers. Vias are created at the beginning of the manufacturing process by drilling holes through the core layers. The via walls are later coated with copper to make them electrically conductive. These vias are labeled as *buried*, *blind* and *through-hole vias* depending on where the holes are located (see Fig. 1.2).

#### **Mounting Technologies**

Two different technologies are primarily used for mounting components on PCBs:

- Through-hole technology (THT), and
- Surface-mount technology (SMT).

THT makes use of devices that have leads to make the electrical contacts. These leads are inserted in holes, which are through-hole vias, and soldered in place (see Fig. 1.2, left). With SMT, the devices instead have metal pads for connecting to the surface of the board (shown in black in Fig. 1.2). Associated with these mounting technologies—THT and SMT—are respectively *through-hole devices* (*THDs*) and *surface-mount(ed) devices* (*SMDs*).



Fig. 1.2 Cross-section of a multilayer board with six routing layers

The two mounting technologies can also be mixed. Component placement systems can handle SMDs much more easily than THDs. In addition, much higher packing densities can be achieved with SMDs, as they are smaller and can be mounted on both sides of a PCB. These advantages make surface-mount technology (SMT) the more widely used approach today.

Besides discrete devices, integrated circuits (ICs) can also be mounted on PCBs. In general, however, they must be "packaged" in an enclosure. Unpackaged ICs (aka *bare dies*) are sometimes mounted directly on PCBs; in this case, however, the stability of the connection is critical due to the different thermal expansion rates of semiconductors and boards.

# 1.1.2 Hybrid Technology

Hybrid technology is an approach in which some of the electrical components are physically separate devices that are then mounted on the carrier substrate, while other components are created directly on the carrier substrate during fabrication. Thus, we get the name "hybrid technology".

A variety of carrier substrates are used in hybrid technology to construct the substrate core; ceramic, glass and quartz are commonly used. SMDs can be mounted on these carrier substrates; however, THDs cannot be mounted, as through holes for mounting purposes are not drilled in these substrates.

Interconnect traces are produced differently on hybrid-technology substrates than on PCBs. The two technologies typically used are *thick-film technology* and *thin-film technology*. In thick-film technology, conductive pastes are applied in a silk-screen printing process and then burnt in. In thin-film technology, the conductive material is vaporized or sputtered<sup>1</sup> onto the substrate. Interconnects are subsequently formed using a photolithographic process much like the process described above for PCBs.

The electrical conductivity of the deposited layers can be adjusted over a large range, which allows electrical resistors to be produced along with interconnects using these technologies. Resistivity values can be finely tuned with a laser; resistance can be increased by trimming the outer regions of the deposited interconnect back perpendicular to the current flow until the desired resistance value is reached.

Interconnect crossings and capacitors can also be realized, such as by alternately stacking conductive and insulating layers. Capacitors can also be created by intertwining comb-like interconnects within a metal layer. An example of this printed capacitor is given in Fig. 1.3.

#### **Example: LTCC Technology**

A widely used variant of the thick-film hybrids is *LTCC* technology, which stands for *low temperature co-fired ceramics*. The LTCC fabrication process is representative of

<sup>&</sup>lt;sup>1</sup>Sputtering is a physical process whereby microscopic particles of a solid material are ejected from its surface by bombarding the solid with high-energy ions.



Fig. 1.3 Fabrication of an LTCC hybrid circuit with printed capacitor, inductor and resistor (LTTC: low temperature co-fired ceramics)

many other technology variants and we will discuss it below. The LTCC fabrication process is depicted in Fig. 1.3a–h.

LTCC technology does not use a prepared ceramic substrate. Instead, fabrication starts with films, in which the ceramic mass in powder form is bonded with other substances. These films are called *green sheets* (a). As we will see below, these films will be made rigid during subsequent processing steps, to produce a board that will become a component in the larger system. First, holes for vias are punched in the sheets (b). These are then filled with conductive paste (c). The interconnect geometries are formed with conductive paste in a silk-screen printing process (d). The green sheets are then stacked on top of one another and laminated by heating them up slightly. They are thus bonded together (e). The stack is then cut to size, pressed together and fired and sintered in an oven (f). Some of the additives escape from the sheet stack during this process and the hybrid shrinks and is sintered to

a ceramic plate, which can contain several interconnect layers in its core. Pressure continues to be applied to the laminated stack during burnout and sintering, so that the shrinking effect is almost completely in the z-axis and the lateral dimensions are not affected. Resistors and conductive surfaces for contacting SMDs and ICs are then printed onto the surface and burnt in (g).

Finally, the SMDs and ICs are mounted (h). The SMDs are fixed in place with a conductive glue or by reflow soldering. The ICs can be mounted unpackaged as bare dies because of the similar thermal expansion rates of carrier substrate (ceramic) and the dies' silicon. They are electrically connected using bond wires running from contact surfaces on the IC, so-called *pads*, to contact surfaces on the carrier.

Among the benefits of hybrid technology over printed circuit technology are: (i) greater mechanical stability (when exposed to extreme shocks and vibrations in automobiles, for example); (ii) higher packing density (due to the use of bare dies); and (iii) better dissipation of thermal losses.

Thermal dissipation is mainly achieved with LTCCs by mounting the hybrid on a heat sink to maximize the thermal coupling over the entire hybrid surface. Good heat dissipation from the top of the hybrid to its bottom can be further improved by deploying so-called *thermal vias*—these are plated-through contacts designed specifically to transmit heat.

While hybrid technology has advantages as noted above (e.g., greater mechanical stability, packing density, and thermal dissipation), it has the disadvantage of higher manufacturing costs, as compared to PCBs.

### 1.1.3 Semiconductor Technology

With the technologies we have discussed thus far, the electronic devices must be wholly or partially added from an external source. With semiconductor technology, on the other hand, an entire electronic circuit can be built as a single unit. Here, all electronic devices and all electrical connections are created in the fabrication process itself. This type of circuit is fully integrated—this is where the name *integrated circuit* (*IC*) originates—in a monolithic semiconductor die. These single, small flat pieces, comprised mostly of silicon, are also called "chips".

We can also use semiconductor technology to construct purely discrete (i.e., single) electronic devices. Typical examples are diodes or active devices, such as transistors and thyristors, for driving very large currents in power electronics. If we examine these devices more closely, we find that they are composed of many similar devices connected in parallel on the chip. Protective circuitry that remains hidden

from view, but which supports the device's performance characteristics, is also often integrated in the chip.

#### What are Semiconductors?—Physical Aspects of Semiconductor Materials

While semiconducting materials can conduct electrical current, their electrical resistivity at room temperature is quite high. However, their conductivity increases exponentially with rising temperature. This thermal characteristic is very different from standard interconnects (metals) and is a key property of semiconductors. We will now delve deeper into the underlying physics.

Free moving charge carriers are required for a current flow. In solids, these charge carriers are electrons. Hence, the question is: "How do we get enough 'free' electrons in semiconductors?" Electrons orbit the atomic nucleus, and their energy levels increase the further they are away from the nucleus. It is also a fact that they can only have certain energy states called *shells* (electron shells) that expand into so-called *bands* in constellations of many atoms. The most exterior band in a substance is also called the *valence band*. If electrons in the valence band (so-called *valence electrons*) can be sufficiently energized to enable them to jump to the next higher band, they can move freely there and thus increase the electrical conductivity of the material. Therefore, this band is also labeled as *conduction band*.

Valence and conduction bands are particularly close together in conductive materials, such as metals; they can even overlap (see the orange area in Fig. 1.4). In this case, many electrons can jump to the conduction band. Hence, metals are excellent conductors. In the case of insulators, on the other hand, the energy gap  $\Delta E$  between the valence and the conduction band (the so-called *band gap* or *band distance*) is so large that it is an almost insurmountable threshold, and there are practically no electrons in the conduction band (blue area in Fig. 1.4).

The main characteristic of semiconductors is that their band gap lies between these two extremes (central green area in Fig. 1.4). On the one hand, this gap is so large that only very few electrons in the valence band have enough energy at



**Fig. 1.4** Materials in the "conductor", "semiconductor" and "insulator" categories as a function of the band gap between valence and conduction band. The values are given for typical semiconductor materials at 300 K. (SiC can take values between 2.4 eV and 3.3 eV, depending on the formed crystal lattice. The value for crystal lattice "6H" is shown.)

room temperature to reach the conduction band. On the other hand, the conduction band is close enough that a temperature rise on the order of a few hundred degrees kelvin above room temperature provides enough energy to increase the number of free electrons, and thus the conductivity, by many orders of magnitude.

The conductivity increases not only because of the free electrons in the conduction band, but also due to the creation of electron holes—known as *defect electrons* or *holes*—in the valence band. These holes can be easily filled with valence electrons from neighboring atoms; the holes then disappear, generating new ones in the "electron-delivering" atoms. A current flow—known as *hole conduction*—can then take place as a result of this chain movement of valence electrons. However, generating free-charge carriers (electrons and holes) by thermal means is not our main concern here, rather we want to highlight the underlying physics for a better understanding of our primary intention.

Let us now take silicon as a typical example (Fig. 1.5). For silicon, the band gap between the lower edge of the conduction band  $E_{\rm C}$  and the top edge of the valence band  $E_{\rm V}$  is given by  $\Delta E = E_{\rm C} - E_{\rm V} = 1.1$  eV. Silicon is 4-valent—in other words, the valence band of a silicon atom contains four electrons. If we replace a silicon atom with an atom of a 5-valent element, such as phosphor, arsenic or antimony, the extra electron will not "fit" into the valence band of the surrounding silicon crystal. It has an energy level  $E_{\rm D}$ , which is just slightly below the silicon conduction band; it is so close to this band that at room temperature it has enough energy to allow it to enter this conduction band (Fig. 1.5, left). Hence, introducing 5-valence impurity atoms into the silicon allows us to increase its conductivity.

Instead of implanting 5-valence impurity atoms, we can also implant 3-valence impurity atoms, such as boron, indium or aluminum, to increase the conductivity. In this case, the impurity atom is at energy level  $E_A$ , which is just slightly above the valence band edge  $E_V$  of silicon; hence, this impurity atom can very easily accept a fourth electron from a neighboring silicon atom (Fig. 1.5, right). The number of holes in the silicon valence band is thus increased. These holes can be viewed as positive charge carriers that are available for current flow, as they can move freely.



**Fig. 1.5** Generating free-charge carriers and thus current flow in a semiconductor (silicon). The creation of free charge carriers by doping with donors is shown on the left and with acceptors on the right, resulting in conduction by electrons (left) and holes (right)

Implanting impurities into a substance is called *doping*. Five-valence impurity atoms are called *donors*, as they release an electron (into the conduction band). They are listed in the column to the right of silicon in the periodic table. Three-valence impurity atoms are known as *acceptors* because of their ability to accept valence electrons from neighboring atoms. They are found in the column to the left of silicon in the periodic table.

A semiconductor containing donors is called *n-doped* and one containing acceptors is called *p-doped*. In areas of n- and p-doping, the additional electrons are trapped by the additional holes. They are said to be *recombined*. Donors and acceptors effectively neutralize each other here.

Any residual donors or acceptors are key to conductivity. The semiconductor is said to be *n*-conductive when donors are in surplus, as the current flow is mostly due to electrons, i.e., negative charge carriers. The semiconductor is said to be *p*-conductive when there are surplus acceptors, as here it is mainly the holes—that can be viewed as positive charge carriers—that cause the current flow. The more abundant charge carriers are called *majority carriers*, while the correspondingly less abundant charge carriers are called *minority carriers*.

#### The Use of Semiconductors

Extremely pure semiconductor material in monocrystalline form is required for producing integrated circuits. All atoms must be physically arranged in a continuous regular structure. This type of structure must be manufactured as it does not occur naturally. It is produced in the form of crystal ingots that are then machined into very thin slices, or *wafers*, which are used for chip fabrication. One wafer can hold a huge number of chips—many hundreds to tens of thousands, depending on the chip and wafer sizes; the chips are all fabricated together on the wafer. At the end of the fabrication process, individual rectangular chips, or *dies*, are cut from the wafer.

Figure 1.6 shows a finished wafer under a microscope. The dies have been separated from one another and are held in place by an adhesive foil (so-called "blue tape").

The most widely used material in the semiconductor industry is silicon. Other semiconducting materials are utilized for special purposes in the industry. Typical examples include: gallium arsenide (GaAs) and silicon germanium (SiGe) in RF circuits; and gallium nitride (GaN) and silicon carbide (SiC) in power electronics. Two 4-valent elements are combined both in SiC and SiGe; a 3-valent element is combined with a 5-valent element in GaAs and GaN. The resulting crystalline structure again behaves like a 4-valent element.

#### **Integrated Devices and Interconnect Traces**

Integrated devices are produced by successively doping a wafer in different ways. The doping operations can be altered in the following ways: (i) different impurities (there are generally several different types of donors and acceptors); (ii) different concentrations (the number of impurity atoms per unit volume); (iii) the penetration depth (up to some  $\mu$ m), and (iv) the doping location.



Fig. 1.6 Wafer under microscope; one chip is contacted by two probes for testing

Integrated devices can be produced using simple processes having less than 10 doping operations. In more complex processes there can be more than 20 doping procedures. For example, an additional layer of the base material is often deposited on the wafer surface between doping with impurity atoms. (This process is called *epitaxy*.)

The doping process is conceptually similar to the photolithographic process for PCBs presented in Sect. 1.1.1, in that masks are again used to selectively alter the composition of the surface of an area. For PCBs we masked areas to create interconnect traces (using subsequent etching, etc.). Here we also use masks, but ones that are far more detailed, with feature sizes that are on the order of nanometers, to selectively deposit atoms on the surface of the wafer, effectively implementing different doped areas.

Different types of electronic devices, such as transistors, diodes and resistors, can be created by implementing differently doped areas. However, care needs to be taken here. When we talk about "devices" on chips, we should be aware that we are only talking about different sections of a monolithic semiconductor die. These sections are designed in such a way that the electrical interaction of the doped areas contained in each section produces the behavior of the desired electronic device. In contrast to the devices on a printed circuit board (PCB), the devices on a chip are never isolated from one another. This can always cause the devices on a chip to interact. These interactions must be considered in the design flow as will be discussed in detail in Chap. 7.



**Fig. 1.7** Sectional view of an IC chip of a typical NPN transistor **a** at the beginning of the process, **b** after "front-end-of-line" (FEOL) and **c** after "back-end-of-line" (BEOL) in the semiconductor process. n-doped regions are drawn in blue, p-doped regions in red. Metallic layers are brown and insulating layers ocher

Figure 1.7 shows a sectional view of a chip. A wafer is slightly less than 1 mm thick. The electrically active parts, however, are located in a very thin layer on one of the two chip surfaces. This area of approximately 1 to 2% of the wafer thickness is depicted in Fig. 1.7; the figure also shows the fabrication stages, which are explained below.

First, the electronic devices are constructed on the wafer surface using doping operations. Semiconductor manufacture begins with a *raw wafer* (see Fig. 1.7a). All doping is carried out in this so-called "front-end-of-line" (*FEOL*) part of IC fabrication<sup>2</sup> and an epitaxial layer is applied as well, if required. The result is exemplified with an NPN bipolar transistor<sup>3</sup> in Fig. 1.7b. The regions doped with impurities are shown in color. We always show n-conductive regions in blue and p-conductive regions in red in this book. The colors indicate that the raw wafer (a) was originally p-doped and the epitaxial layer (b, on top of the raw wafer) n-doped.

Second, the electrical devices are interconnected by constructing metallic and insulating layers. This process is commonly labeled as "back-end-of-line" (*BEOL*). Here too a photolithographic process involving masks is used to create interconnects. This process is also conceptually similar to the way interconnects were created on PCBs (as presented in Sect. 1.1.1), but here the masks are again far more detailed with nanometer-sized features. Insulating layers (shown in ocher) and metallic layers (brown) are alternately stacked on top of one another and structured in the back-end-of-line (BEOL) part of fabrication. *Interconnects* and *through contacts* are formed in this step.

<sup>&</sup>lt;sup>2</sup>While the term "front-end-of-line" (FEOL) refers to the first portion of any IC fabrication where the individual devices are patterned, "back-end-of-line" (BEOL) comprises the subsequent deposition of metal interconnect layers. Both are discussed in Chap. 2.

<sup>&</sup>lt;sup>3</sup>Bipolar transistors are devices whose operation depends on the two types of charge carriers (electrons and holes). We will cover these devices and their operation more fully in Chap. 6.

The result of the BEOL is shown in Fig. 1.7c for two interconnect layers. The devices are electrically connected on the silicon surface through *contact holes* (*contacts*) in the bottom insulating layer. The through contacts between neighboring metal layers are known as *vias* in IC chips as well as in PCBs. (Please note that we use the term *through contact* to label any vertical connection between layers. Referring to ICs, we further differentiate between *contacts* that connect the devices to the (first) metal layer and *vias* that connect (two) metal layers.)

As illustrated in Fig. 1.7, photolithography is used to create all structures on the chip, regardless of whether it is delineating doping areas in the FEOL (front-end-of-line), or the formation of vias and interconnects in the BEOL (back-end-of-line). Photolithography plays a key role in fabrication, as we also saw in the production of PCBs in Sect. 1.1.1. We shall cover the process steps in semiconductor fabrication in detail in Chap. 2.

# **1.2 Integrated Circuits**

### **1.2.1** Importance and Characteristics

Since the first integrated circuits (ICs) appeared in the 1960s, microelectronics has developed at a breathtaking pace. It has long become a key technology across all our technological advances. It has a huge effect on all our lives and will continue to do so. What are the drivers behind this massive relentless creative power? We will now dig deeper into the important properties of ICs that continue to propel these developments, and try to answer this question.

The idea of integrating electronic circuits on a single piece of semiconductor material was first expressed towards the end of the 1950s by Jack Kilby [3] and Robert Noyce [5] independently of one another. The first commercial semiconductor chip was produced in 1961: it was a logical memory element (called a *flipflop*) with four transistors and five resistors [1].

This was the birth of microelectronics and the beginning of the modern computing era. From that time forth, semiconductor technology went from strength to strength, accompanied by unabating IC miniaturization. This miniaturization is the driver for a series of effects, that are mutually supportive, and whose cumulate effect, upon closer scrutiny, continues to amaze.

The on-going reduction in the footprint of individual devices means the chips use less power, operate faster, and can accommodate an increasing number of functions as the individual devices can be packed more densely. These are all logical developments that are easy to understand. Why the extra functions should be cheaper is not so easy to fathom though. We can explain it as follows. It is a fact that semiconductor technologies and chip space become more expensive with increasing miniaturization. Nonetheless, the extra costs are more than recouped as individual functions require less chip space due to the miniaturization. You get more bang for your buck effectively "more functionality for the same price"—with each new chip generation.

There is another effect that is less obvious but is nonetheless a very important aspect of the chip success story. Ever increasing integration density in chips has a very positive effect on the reliability of electronic systems: every incremental reduction in the number of solder points and every discrete device you can do without reduces the probability of a system failure. An entire chip is only a single device as far as the downtime risk goes. (Recall that integrated devices are essentially only sections of a semiconductor chip.) The semiconductor chip thus represents a single device, and a single point of failure; as a result, systems built using such semiconductor chips have fewer possible points of failure, which leads to higher reliability.

Let us try to imagine the implications of these effects: If you split the electronics from a modern mobile phone into discrete (i.e., individual) electronic components, and place them on PCBs, for example, you would need a huge industrial building to hold them. This monstrous "device" would not only be unwieldy and therefore useless, it would also be prohibitively expensive and highly unreliable. If a single device or connection in this hypothetical system failed, the system would fail as well. It would likely be permanently down, which would mean that (on the bright side) at least you wouldn't need the entire power plant required to run it!

Let us list these six effects again: continued improvements in microelectronics make electronic systems smaller, faster, more economical, more intelligent, cheaper and more reliable.<sup>4</sup> Normally, these performance characteristics cannot all be improved together—as evidenced in other technology sectors, such as the automotive industry, for example. They typically hamper each other, and engineers must find the best compromise for each use case. In contrast, all these performance characteristics have improved in unison in microelectronics, which explains its persistent and sustainable success.

# 1.2.2 Analog, Digital and Mixed-Signal Circuits

Today's chips are highly complex. The first thing to be aware of is that most of them contain both digital and analog circuits. Not only do these two types of circuits operate fundamentally differently from one another, they differ greatly in their suitability for existing design flows and semiconductor technologies.

Let us look at digital circuits first. They are much more technically amenable than their analog counterparts because they handle exclusively discrete signal values. These typically are binary signals, with only two differentiable values, which are

<sup>&</sup>lt;sup>4</sup>We should mention here that downscaling to lower technology nodes in semiconductor fabrication has reached a point where aging effects are becoming increasingly critical. One of the more acute concerns is interconnect degradation by migration effects, in which the electrical current flowing through the IC can slowly erode the miniature physical structures. Preventive measures for these effects are needed especially in the physical design flow. We shall deal with this topic fully in Chap. 7.